
2SD655

Silicon NPN Epitaxial

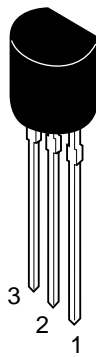
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Application

Low frequency power amplifier, Muting

Outline

TO-92 (1)



1. Emitter
2. Collector
3. Base

2SD655

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	30	V
Collector to emitter voltage	V_{CEO}	15	V
Emitter to base voltage	V_{EBO}	5	V
Collector current	I_C	0.7	A
Collector peak current	$i_{C(\text{peak})}$	1.0	A
Collector power dissipation	P_C	500	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

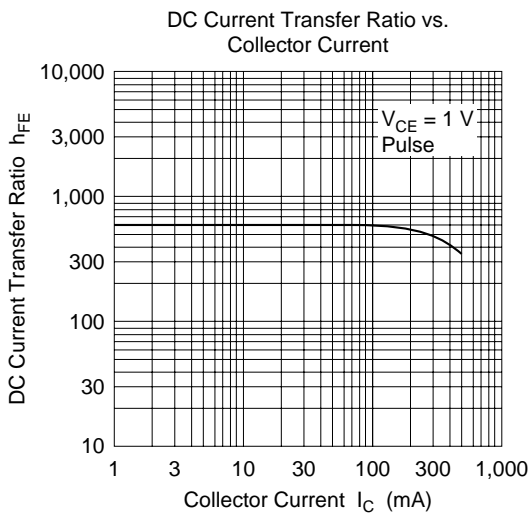
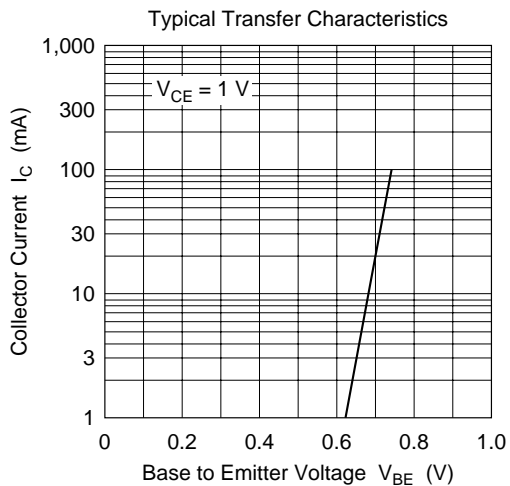
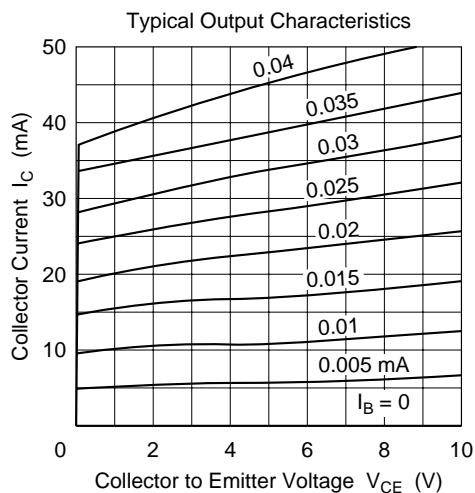
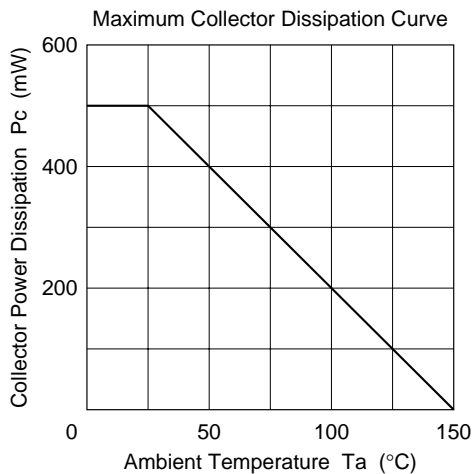
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	30	—	—	V	$I_C = 10 \mu\text{A}, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	15	—	—	V	$I_C = 1 \text{ mA}, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	5	—	—	V	$I_E = 10 \mu\text{A}, I_C = 0$
Collector cutoff current	I_{CBO}	—	—	1.0	μA	$V_{CB} = 20 \text{ V}, I_E = 0$
Base to emitter voltage	V_{BE}	—	—	1.0	V	$V_{CE} = 1 \text{ V}, I_C = 150 \text{ mA}$
Collector to emitter saturation voltage	$V_{CE(\text{sat})}$	—	0.15	0.5	V	$I_C = 500 \text{ mA}, I_B = 50 \text{ mA}^{*2}$
DC current transfer ratio	h_{FE}^{*1}	250	—	1200		$V_{CE} = 1 \text{ V}, I_C = 150 \text{ mA}^{*2}$
Gain bandwidth product	f_T	—	250	—	MHz	$V_{CE} = 1 \text{ V}, I_C = 150 \text{ mA}$

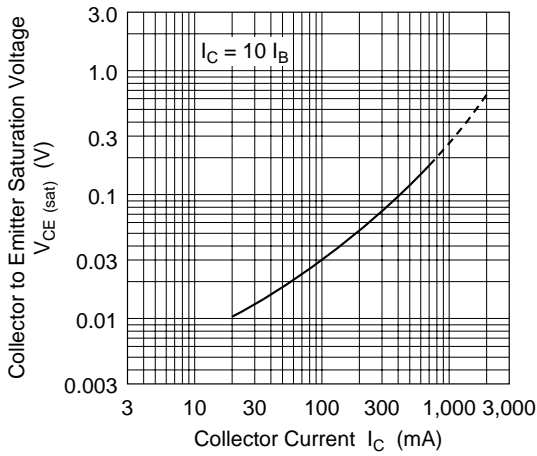
Notes: 1. The 2SD655 is grouped by h_{FE} as follows.

2. Pulse test

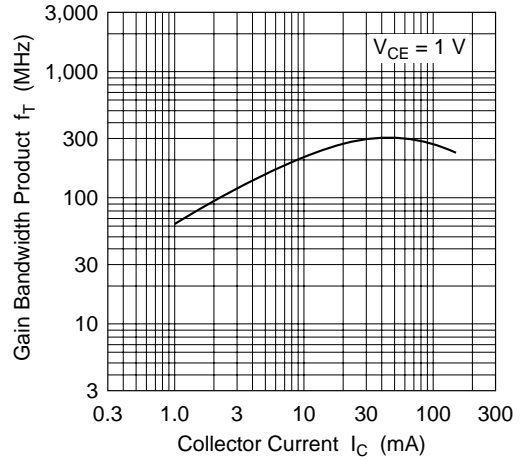
D	E	F
250 to 500	400 to 800	600 to 1200



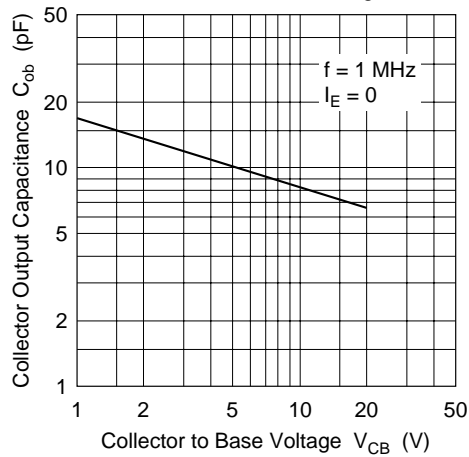
Collector to Emitter Saturation Voltage vs. Collector Current

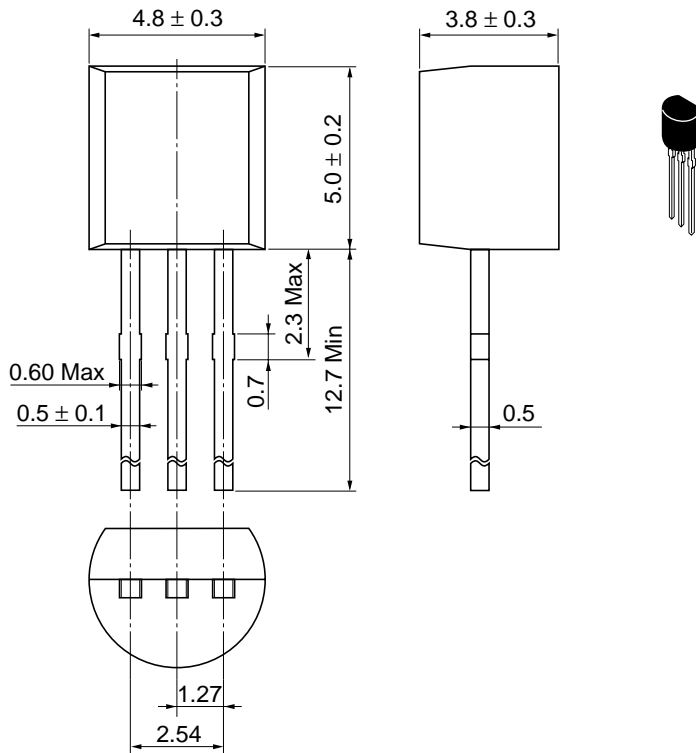


Gain Bandwidth Product vs. Collector Current



Collector Output Capacitance vs. Collector to Base Voltage





Hitachi Code	TO-92 (1)
JEDEC	Conforms
EIAJ	Conforms
Weight (reference value)	0.25 g

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Hitachi, Ltd.

Semiconductor & Integrated Circuits.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL North America : <http://semiconductor.hitachi.com/>
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For further information write to:

Hitachi Semiconductor
(America) Inc.
179 East Tasman Drive,
San Jose, CA 95134
Tel: <1> (408) 433-1990
Fax: <1> (408) 433-0223

Hitachi Europe GmbH
Electronic components Group
Dornacher Straße 3
D-85622 Feldkirchen, Munich
Germany
Tel: <49> (89) 9 9180-0
Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.
Electronic Components Group.
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA, United Kingdom
Tel: <44> (1628) 585000
Fax: <44> (1628) 778322

Hitachi Asia Pte. Ltd.
16 Collyer Quay #20-00
Hitachi Tower
Singapore 049318
Tel: 535-2100
Fax: 535-1533

Hitachi Asia Ltd.
Taipei Branch Office
3F, Hung Kuo Building, No.167,
Tun-Hwa North Road, Taipei (105)
Tel: <886> (2) 2718-3666
Fax: <886> (2) 2718-8180

Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower, World Finance Centre,
Harbour City, Canton Road, Tsim Sha Tsui,
Kowloon, Hong Kong
Tel: <852> (2) 735 9218
Fax: <852> (2) 730 0281
Telex: 40815 HITEC HX

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